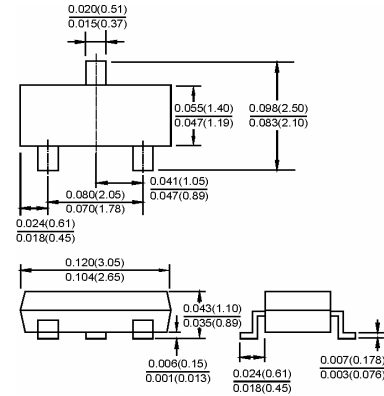

**SOT-23**

**Features**

- ✧ Power dissipation:  $P_{CM} = 0.35 \text{ W}$  ( $T_{amb}=25^{\circ}\text{C}$ )
- ✧ Collector current:  $I_{CM} = 0.2 \text{ A}$
- ✧ Collector-base voltage:  $V_{(BR)CBO} = 400 \text{ V}$
- ✧ Operating and storage junction temperature range  
 $T_J, T_{stg}: -55^{\circ}\text{C}$  to  $+150^{\circ}\text{C}$

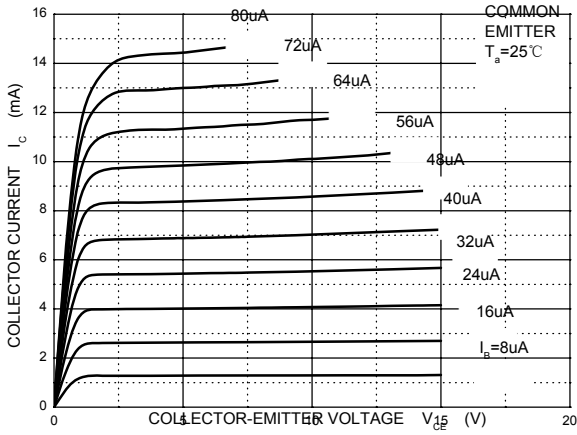
Dimensions in inches and (millimeters)

**ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}\text{C}$  unless otherwise specified)**

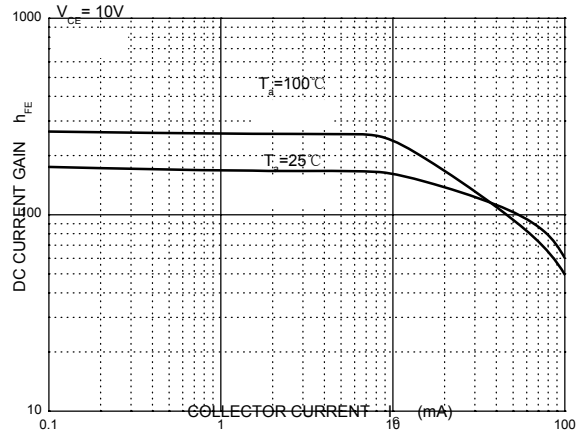
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, I_B = 0$	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = 400\text{V}, I_E = 0$			0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE} = 400\text{V}$			5	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 4\text{V}, I_C = 0$			0.1	$\mu\text{A}$
DC current gain	$H_{FE(1)}$	$V_{CE} = 10\text{V}, I_C = 10\text{mA}$	50		200	
	$H_{FE(2)}$	$V_{CE} = 10\text{V}, I_C = 1\text{mA}$	40			
	$H_{FE(3)}$	$V_{CE} = 10\text{V}, I_C = 100\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 1\text{mA}$			0.5	V
	$V_{CE(sat)}$	$I_C = 50\text{mA}, I_B = 5\text{mA}$			0.75	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10\text{mA}, I_B = 1\text{mA}$			0.75	V
Transition frequency	$f_T$	$V_{CE} = 20\text{V}, I_C = 10\text{mA}$ $f = 30\text{MHz}$	50			MHz

<b>MARKING</b>	3D
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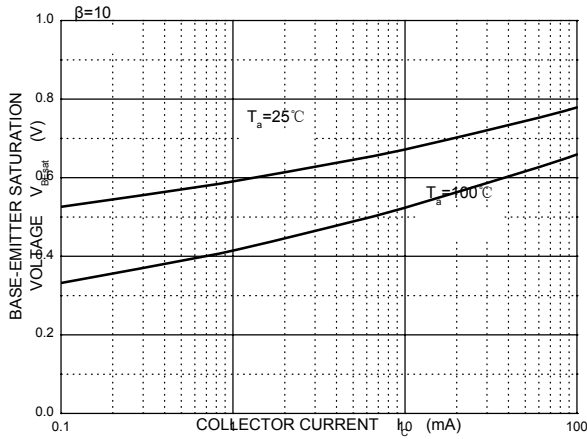
Static Characteristic



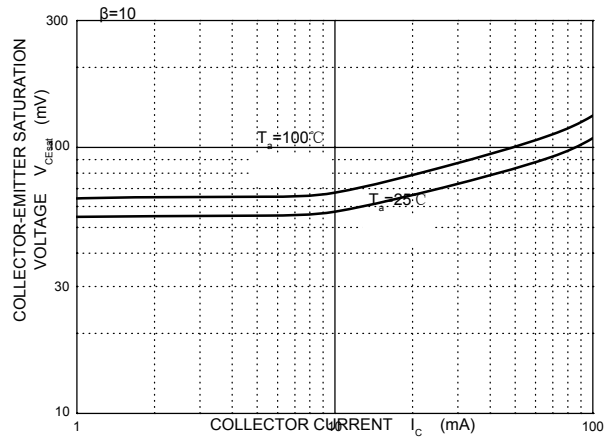
$h_{FE} \text{ --- } I_c$



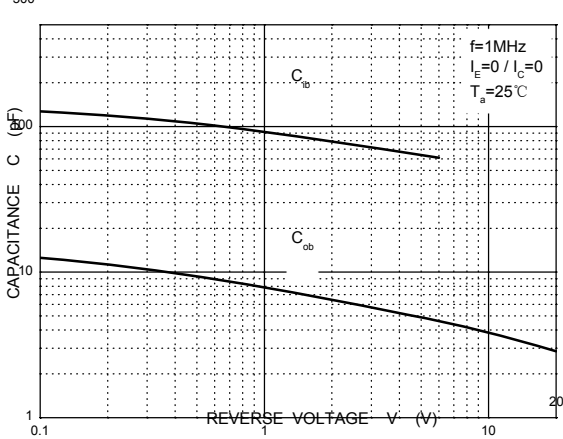
$V_{BEsat} \text{ --- } I_c$



$V_{CEsat} \text{ --- } I_c$



$C_{ob} / C_{ib} \text{ --- } V_{CB} / V_{EB}$



$P_c \text{ --- } T_a$

